

Silicon PNP Power Transistors

MJW21191

DESCRIPTION

www.datasheet4u.com

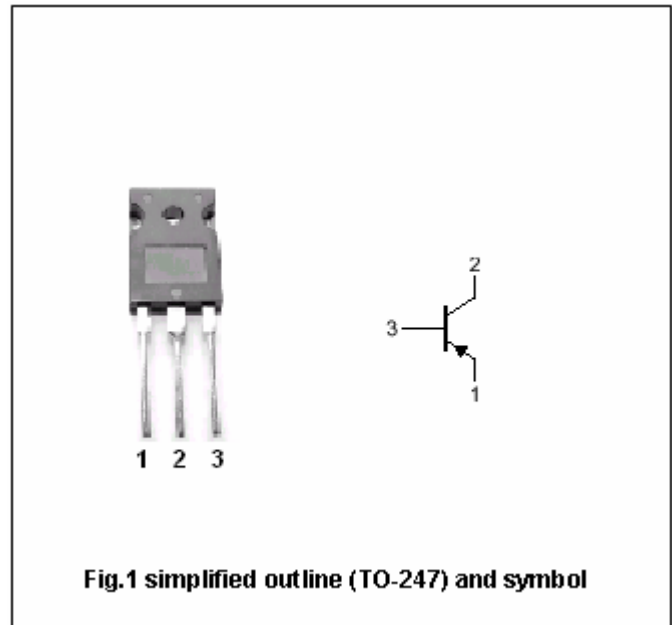
- With TO-247 package
- Complement to type MJW21192
- Wide area of safe operation

APPLICATIONS

- Designed for power audio output, high power drivers in audio amplifiers

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

ABSOLUTE MAXIMUM RATINGS($T_C=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-8	A
I_{CM}	Collector current-peak		-16	A
I_B	Base current		-2	A
P_D	Total power dissipation	$T_C=25^\circ\text{C}$	100	W
T_j	Junction temperature		-65~150	$^\circ\text{C}$
T_{stg}	Storage temperature		-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R_{th-j-c}	Thermal resistance from junction to case	0.65	$^\circ\text{C}/\text{W}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =-10mA ; I _B =0	-150			V
V _{CE(sat)-1}	Collector-emitter saturation voltage	I _C =-4A; I _B =-0.4A			-1.0	V
V _{CE(sat)-2}	Collector-emitter saturation voltage	I _C =-8A; I _B =-1.6A			-2.0	V
V _{BE(ON)}	Base-emitter on voltage	I _C =-4A ; V _{CE} =-2V			-2.0	V
I _{CES}	Collector cut-off current	V _{CB} =-150V; I _E =0			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-10	μA
h _{FE-1}	DC current gain	I _C =-4A ; V _{CE} =-2V	15		100	
h _{FE-2}	DC current gain	I _C =-8A ; V _{CE} =-2V	5			
f _T	Transition frequency	I _C =-1.0A ; V _{CE} =-10V, f=1MHz	4.0			MHz

